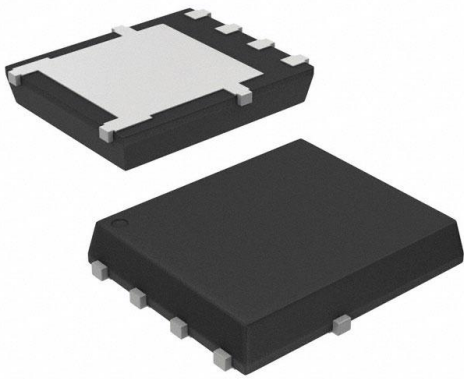


NTMFS6D1N08HT1G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	NTMFS6D1N08HT1G-DG
Manufacturer	onsemi
Manufacturer Product Number	NTMFS6D1N08HT1G
Description	MOSFET N-CH 80V 17A/89A 5DFN
Detailed Description	N-Channel 80 V 17A (Ta), 89A (Tc) 3.8W (Ta), 104W (Tc) Surface Mount 5-DFN (5x6) (8-SOFL)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

NTMFS6D1N08HT1G

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

80 V

Drive Voltage (Max Rds On, Min Rds On):

6V, 10V

Vgs(th) (Max) @ Id:

4V @ 120 μ A

Vgs (Max):

\pm 20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

5-DFN (5x6) (8-SOFL)

Base Product Number:

NTMFS6

Manufacturer:

onsemi

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

17A (Ta), 89A (Tc)

Rds On (Max) @ Id, Vgs:

5.5mOhm @ 20A, 10V

Gate Charge (Qg) (Max) @ Vgs:

32 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

2085 pF @ 40 V

Power Dissipation (Max):

3.8W (Ta), 104W (Tc)

Mounting Type:

Surface Mount

Package / Case:

8-PowerTDFN, 5 Leads

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

MOSFET – Power, Single, N-Channel

80 V, 5.5 mΩ, 89 A

NTMFS6D1N08H

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free, Beryllium Free and are RoHS Compliant

Typical Applications

- Synchronous Rectification
- AC-DC and DC-DC Power Supplies
- AC-DC Adapters (USB PD) SR
- Load Switch

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	80	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	I_D	89	A
			P_D	104	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	I_D	17	A
			P_D	3.8	W
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	468	A	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	87	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_{AV} = 5.9 \text{ A}$)		E_{AS}	465	mJ	
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)		T_L	300	$^\circ\text{C}$	

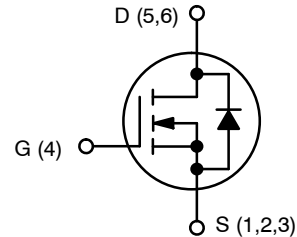
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

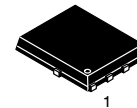
Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	1.44	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	40	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using 1 in² pad size, 1 oz. Cu pad.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	5.5 mΩ @ 10 V	89 A
	8.0 mΩ @ 6 V	

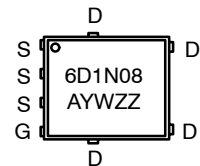


N-CHANNEL MOSFET



DFN5
(SO-8FL)
CASE 488AA
STYLE 1

MARKING DIAGRAM



- A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS6D1N08HT1G	DFN5 (Pb-Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTMFS6D1N08H**ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		43.8		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 120\ \mu\text{A}$	2.0		4.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		-7.08		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		4.5	5.5	$\text{m}\Omega$
		$V_{GS} = 6\text{ V}, I_D = 10\text{ A}$		6.4	8.0	
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		80		S
Gate-Resistance	R_G	$T_A = 25^\circ\text{C}$		1.0		Ω

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 40\text{ V}$		2085		pF	
Output Capacitance	C_{OSS}			300			
Reverse Transfer Capacitance	C_{RSS}			10			
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 6\text{ V}, V_{DS} = 40\text{ V}, I_D = 30\text{ A}$		10		nC	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}, I_D = 30\text{ A}$		32		nC	
			Gate-to-Source Charge	Q_{GS}	10		
			Gate-to-Drain Charge	Q_{GD}	6		
			Plateau Voltage	V_{GP}	5		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 64\text{ V}, I_D = 30\text{ A}, R_G = 2.5\ \Omega$		18		ns
Rise Time	t_r			50		
Turn-Off Delay Time	$t_{d(OFF)}$			48		
Fall Time	t_f			39		

DRAIN-SOURCE DIODE CHARACTERISTICS

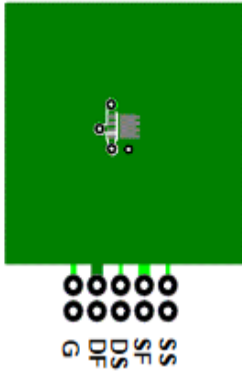
Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 20\text{ A}$	$T_J = 25^\circ\text{C}$		0.8	1.2	V
			$T_J = 125^\circ\text{C}$		0.7		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, di_S/dt = 100\text{ A}/\mu\text{s}, I_S = 20\text{ A}$		49		ns	
Reverse Recovery Charge	Q_{RR}			60		nC	
Charge Time	t_a	$V_{GS} = 0\text{ V}, di_S/dt = 100\text{ A}/\mu\text{s}, I_S = 20\text{ A}$		30		ns	
Discharge Time	t_b			19		ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures

4. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

NTMFS6D1N08H



a) 53°C/W when mounted on a 1 in² pad of 2 oz copper.



b) 125°C/W when mounted on a minimum pad of 2 oz copper.

5. Pulse Test: pulse width < 300 μ s, duty cycle < 2%.
6. E_{AS} of 465 mJ is based on started $T_J = 25^\circ\text{C}$, $I_{AS} = 5.9$ A, $V_{DD} = 80$ V, $V_{GS} = 10$ V. 100% test at $I_{AS} = 8.4$ A.
7. As an N-ch device, the negative V_{GS} rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

NTMFS6D1N08H

TYPICAL CHARACTERISTICS

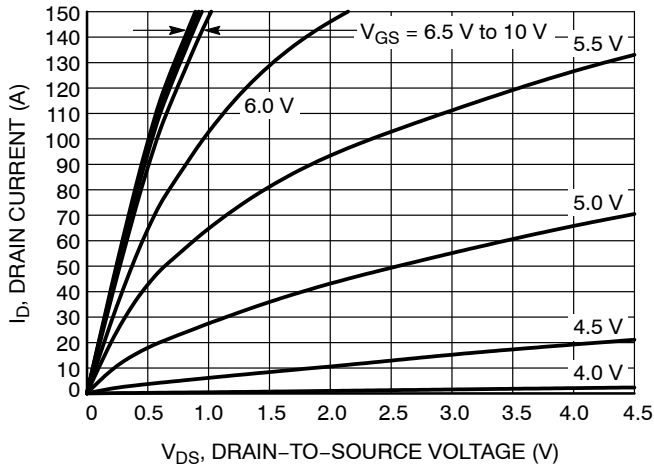


Figure 1. On-Region Characteristics

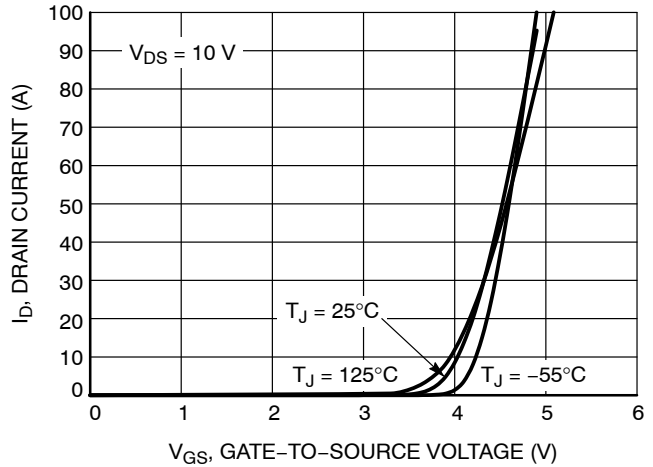


Figure 2. Transfer Characteristics

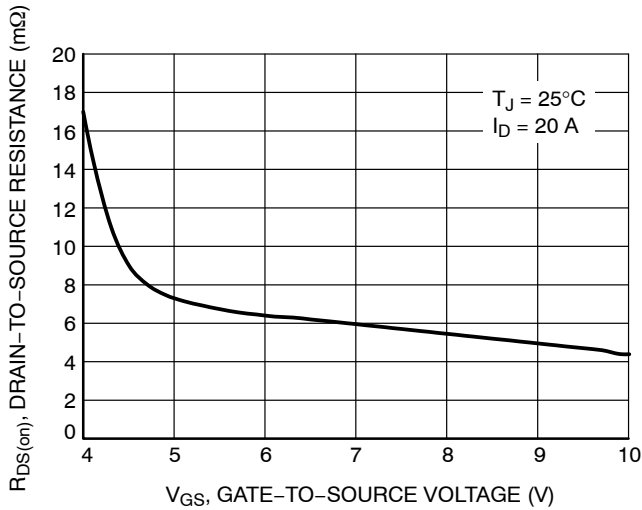


Figure 3. On-Resistance vs. Gate-to-Source Voltage

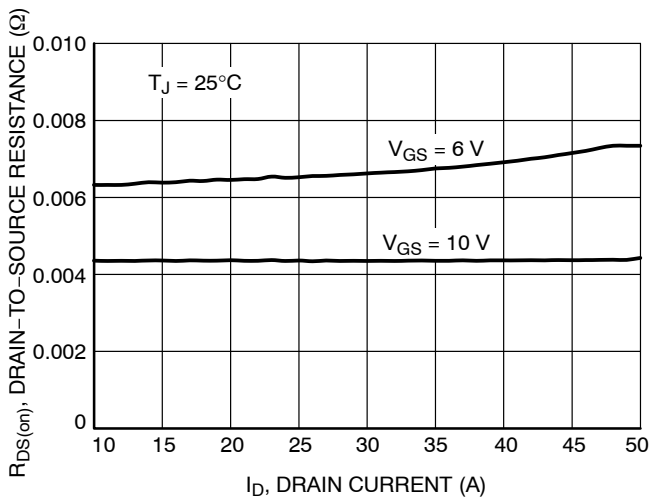


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

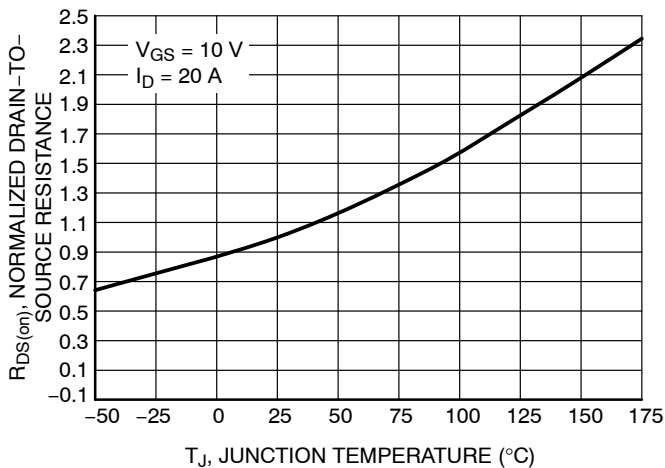


Figure 5. On-Resistance Variation with Temperature

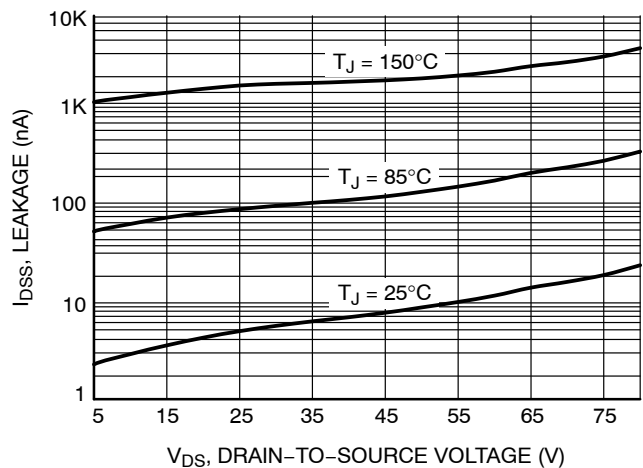


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTMFS6D1N08H

TYPICAL CHARACTERISTICS

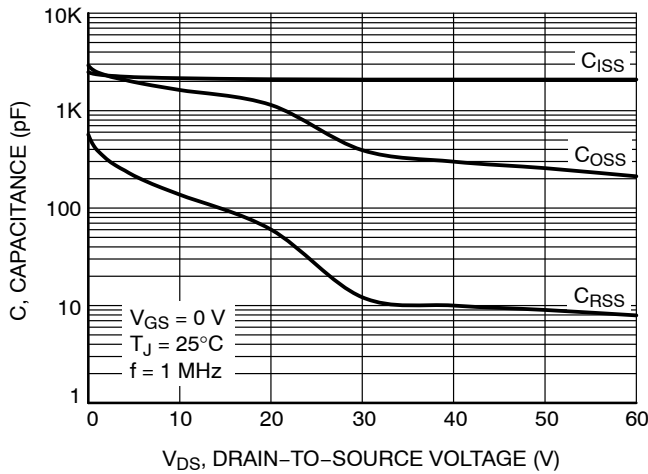


Figure 7. Capacitance Variation

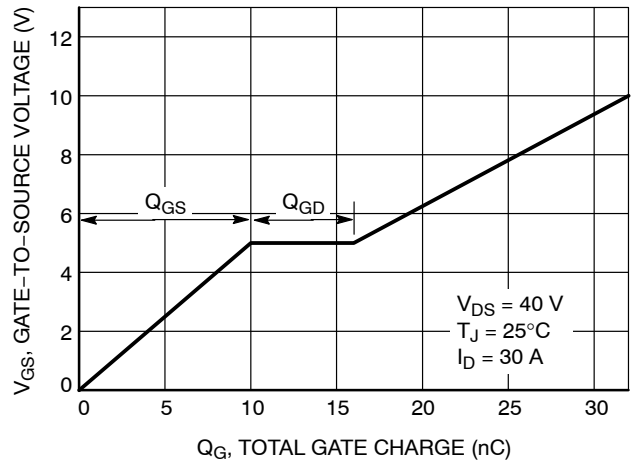


Figure 8. Gate-to-Source Voltage vs. Total Charge

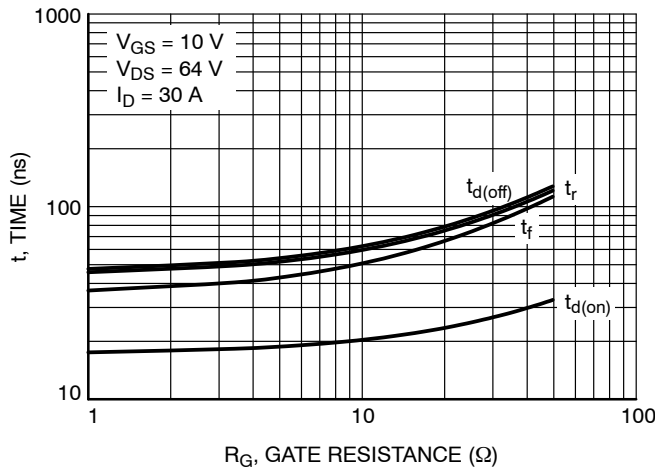


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

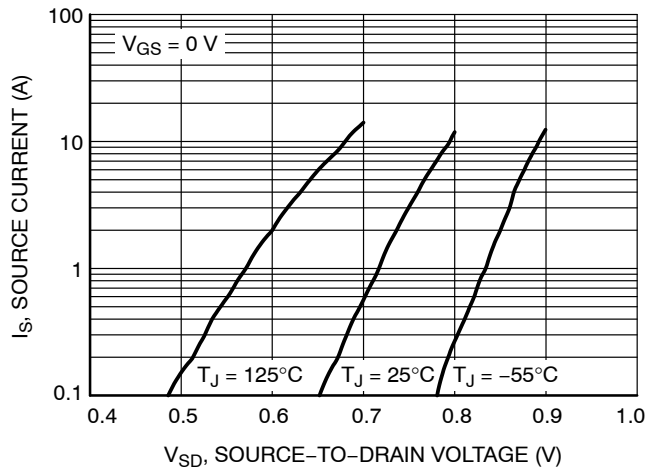


Figure 10. Diode Forward Voltage vs. Current

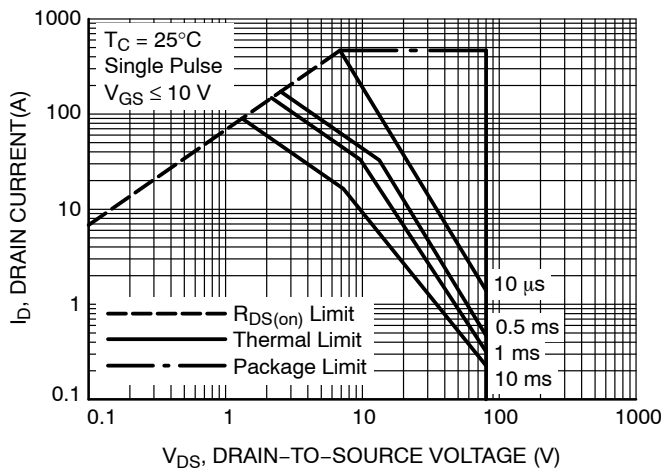


Figure 11. Maximum Rated Forward Biased Safe Operating Area

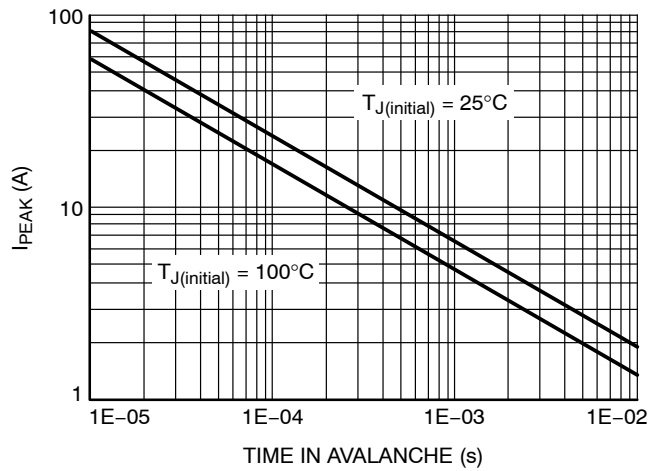


Figure 12. I_{PEAK} vs. Time in Avalanche

NTMFS6D1N08H

TYPICAL CHARACTERISTICS

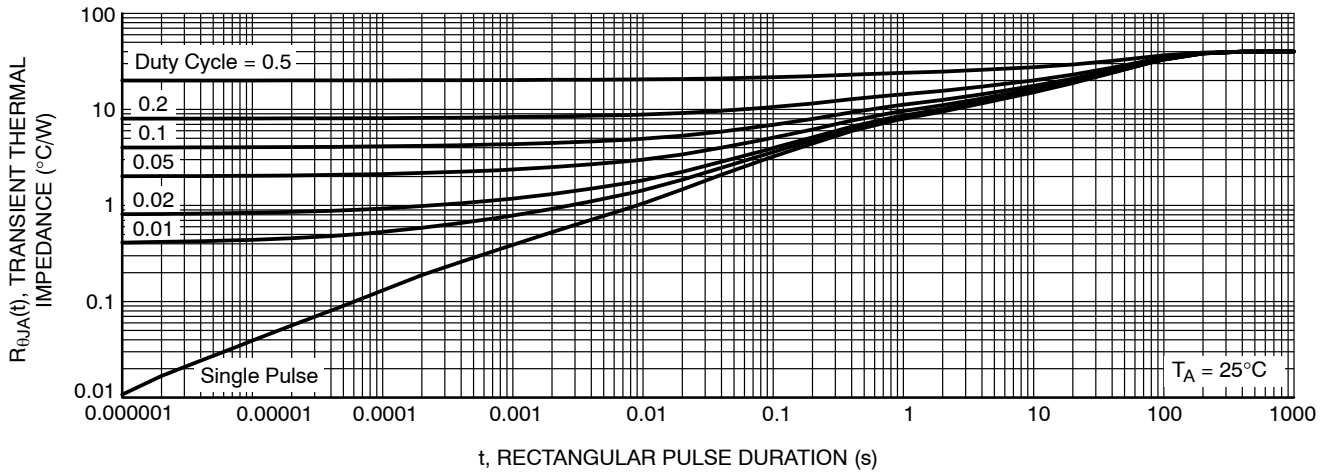


Figure 13. Thermal Response

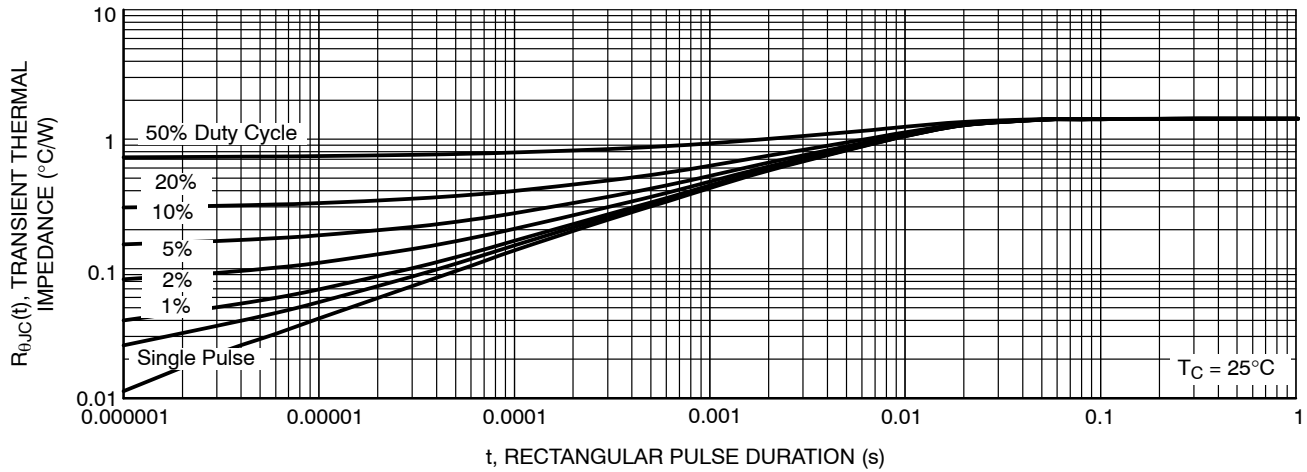
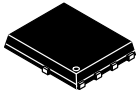


Figure 14. Thermal Response



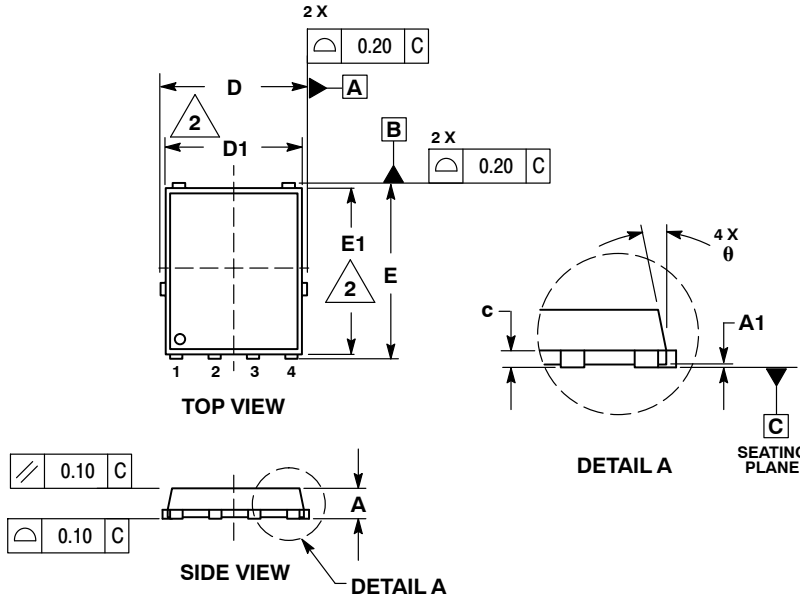
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



1
SCALE 2:1

**DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N**

DATE 25 JUN 2018

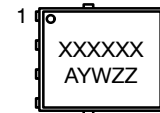


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

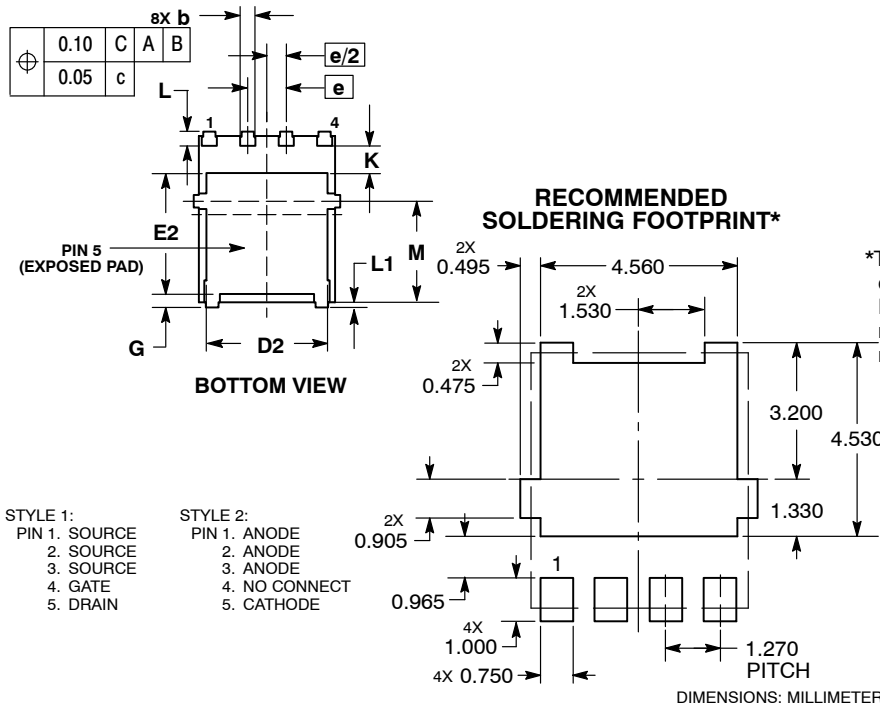
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



- STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
- STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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